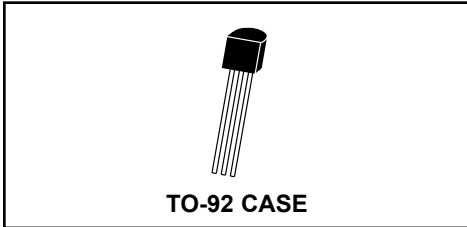


**CS92-2M
CS92-2N***

**SILICON CONTROLLED RECTIFIER
2.0 AMP, 600 THRU 800 VOLTS**



CentralTM

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CS92-2M and CS92-2N are epoxy molded Silicon Controlled Rectifiers designed for sensing circuit applications and control systems.

MARKING CODE: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

	<u>SYMBOL</u>	<u>CS92-2M</u>	<u>CS92-2N*</u>	<u>UNITS</u>
Peak Repetitive Off-State Voltage	V_{DRM}, V_{RRM}	600	800	V
RMS On-State Current ($T_C=60^\circ\text{C}$)	$I_T(\text{RMS})$		2.0	A
Peak One Cycle Surge ($t=10\text{ms}$)	I_{TSM}		10	A
I^2t Value for Fusing ($t=10\text{ms}$)	I^2t		0.24	A^2s
Peak Gate Power ($t_p=10\mu\text{s}$)	P_{GM}		2.0	W
Average Gate Power Dissipation	$P_G(\text{AV})$		0.1	W
Peak Gate Current ($t_p=10\mu\text{s}$)	I_{GM}		1.0	A
Peak Gate Voltage ($t_p=10\mu\text{s}$)	V_{GM}		8.0	V
Storage Temperature	T_{stg}	-40 to +150		$^\circ\text{C}$
Junction Temperature	T_J	-40 to +125		$^\circ\text{C}$
Thermal Resistance	θ_{JA}	200		$^\circ\text{C/W}$
Thermal Resistance	θ_{JC}	100		$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

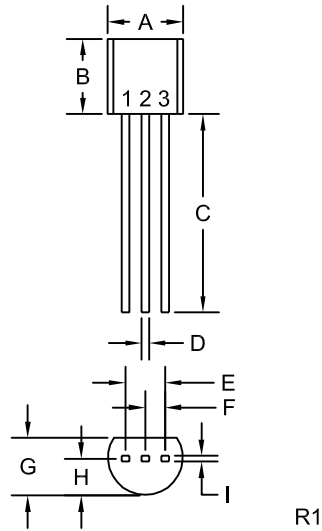
<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>TYP</u>	<u>MAX</u>	<u>UNITS</u>
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, R_{GK}=1\text{K}\Omega$			10	μA
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, R_{GK}=1\text{K}\Omega, T_C=125^\circ\text{C}$			100	μA
I_{GT}	$V_D=12\text{V}$		20	200	μA
I_H	$I_T=100\text{mA}, R_{GK}=1\text{K}\Omega$			2.0	mA
V_{GT}	$V_D=12\text{V}$			0.8	V
V_{TM}	$I_{TM}=4.0\text{A}, t_p=380\mu\text{s}$		1.4	1.7	V
dv/dt	$V_D=2/3 V_{DRM}, R_{GK}=1\text{K}\Omega, T_C=125^\circ\text{C}$	10			V/ μs

* Available on request. Please consult factory.

R0 (22-April 2004)

SILICON CONTROLLED RECTIFIER
2.0 AMP, 600 THRU 800 VOLTS

TO-92 CASE - MECHANICAL OUTLINE



R1

LEAD CODE:

- 1) CATHODE
- 2) GATE
- 3) ANODE

MARKING CODE:

FULL PART NUMBER

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.500	-	12.70	-
D	0.016	0.022	0.41	0.56
E	0.100		2.54	
F	0.050		1.27	
G	0.125	0.165	3.18	4.19
H	0.080	0.105	2.03	2.67
I	0.015		0.38	

TO-92 (REV: R1)

R0 (22-April 2004)